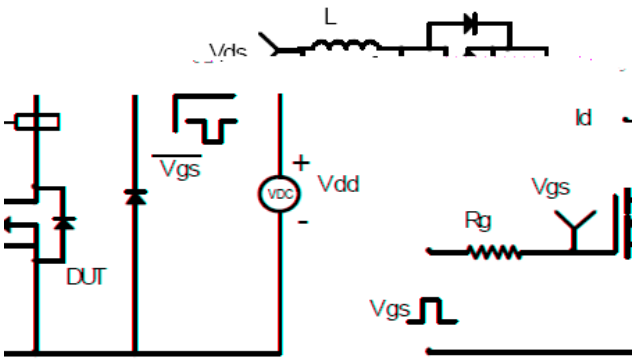
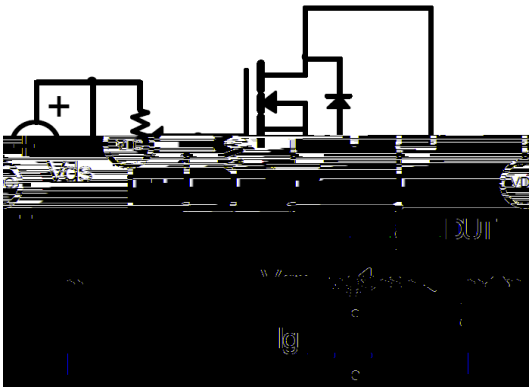
Thermal Resistance

Test Circuits and Waveforms

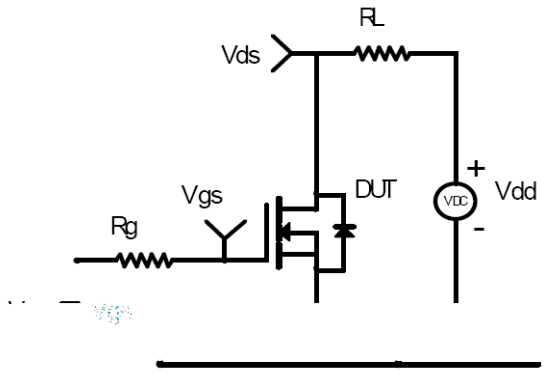
EAS Test Circuit:



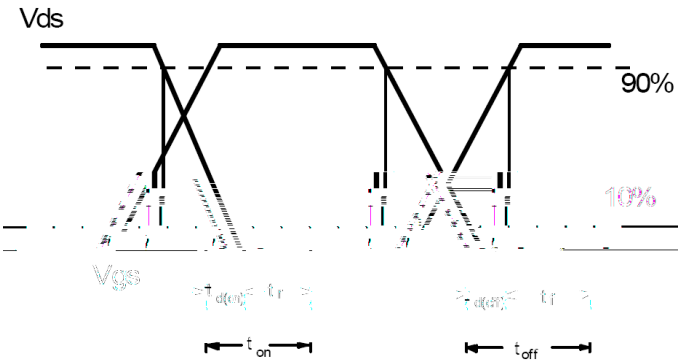
Gate Charge Test Circuit:



Switching Time Test Circuit:



Switching Waveforms:



Notes:

Calculated continuous current based on maximum allowable junction temperature.

Repetitive rating; pulse width limited by max. junction temperature.

The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.

The value of $R_{\theta A}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with TA =25

Typical Electrical and Thermal Characteristics

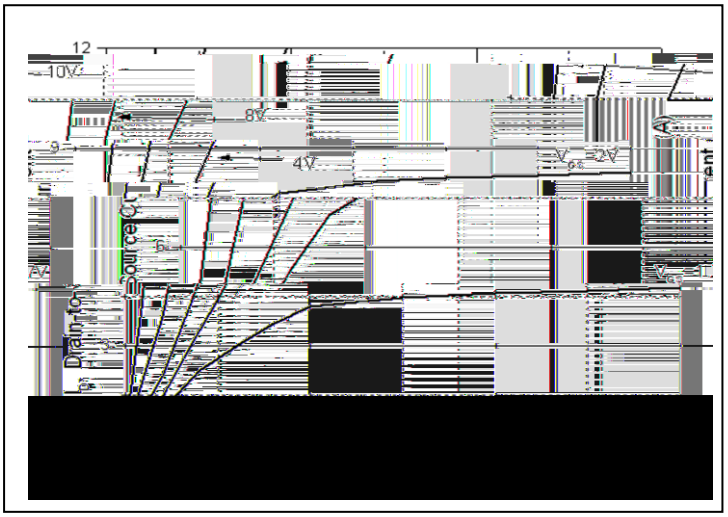


Figure1.Typical Output Characteristics

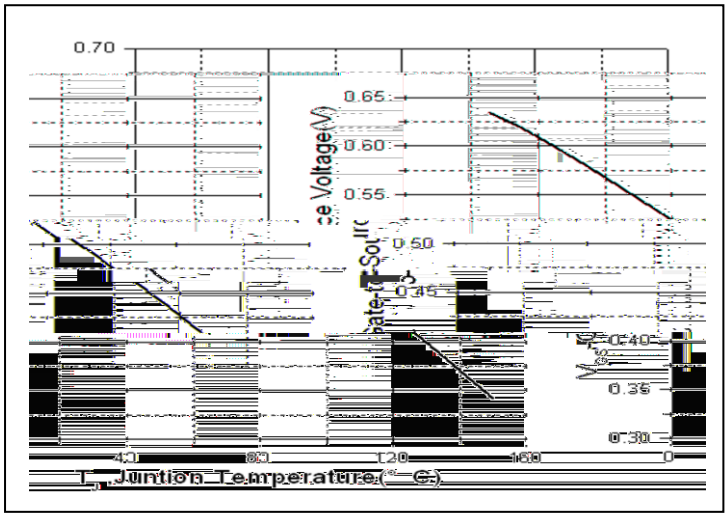


Figure2. Gate to Source Cut-off

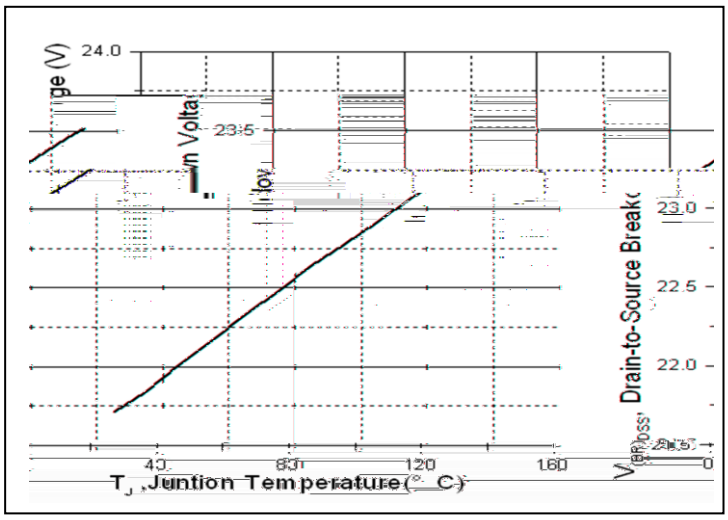


Figure3. Drain-to-Source Breakdown Voltage vs. Junction Temperature

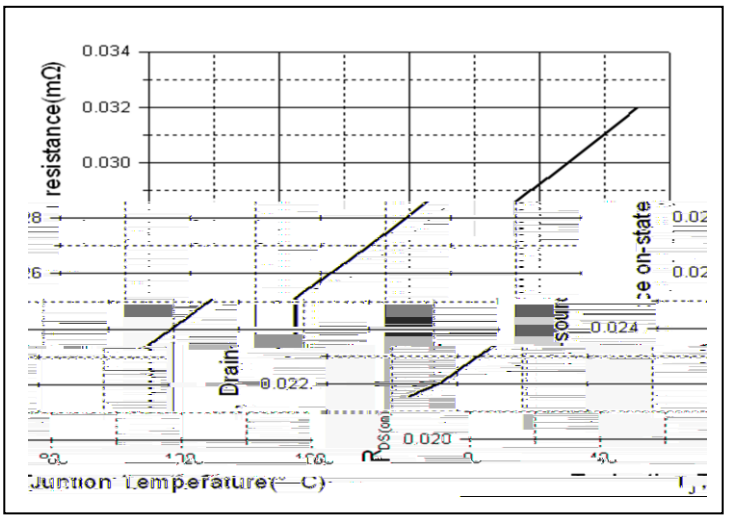


Figure4.$R_{DS(on)}$ vs. Junction Temperature

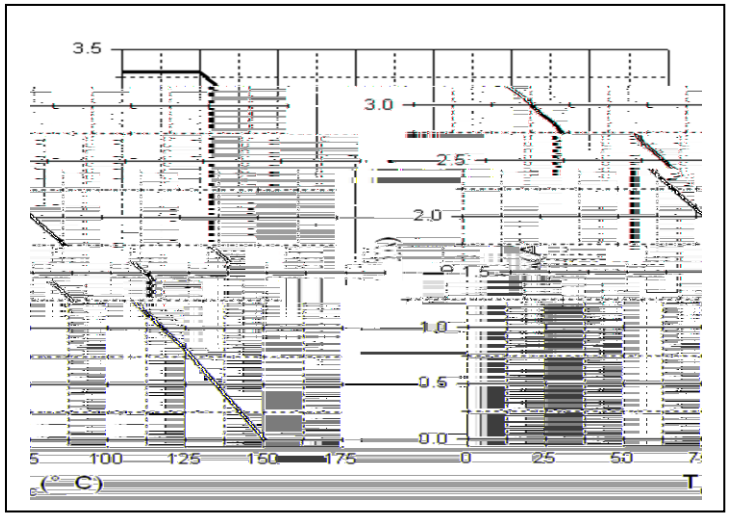


Figure5. Drain Current vs. Case Temperature

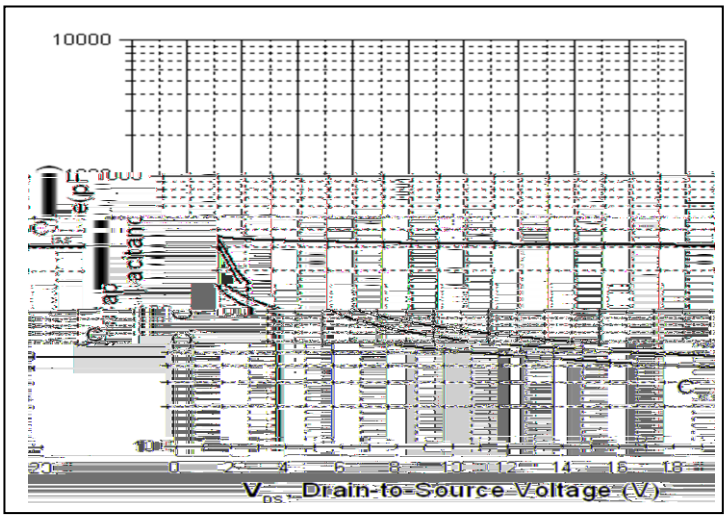
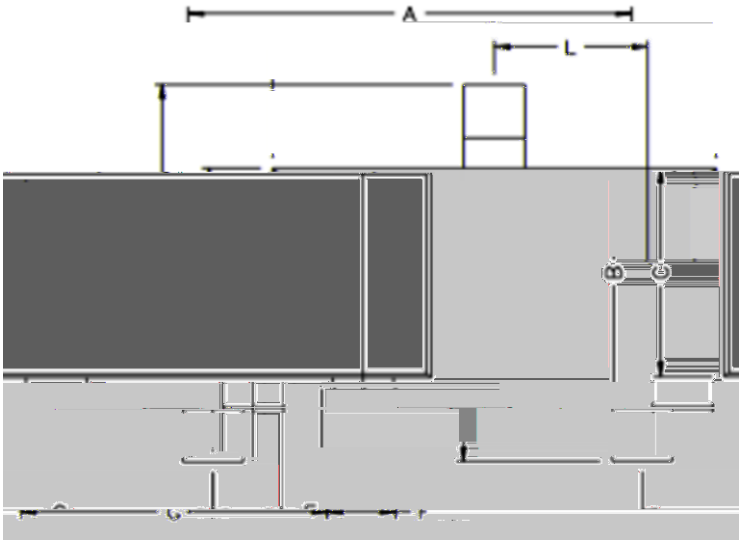
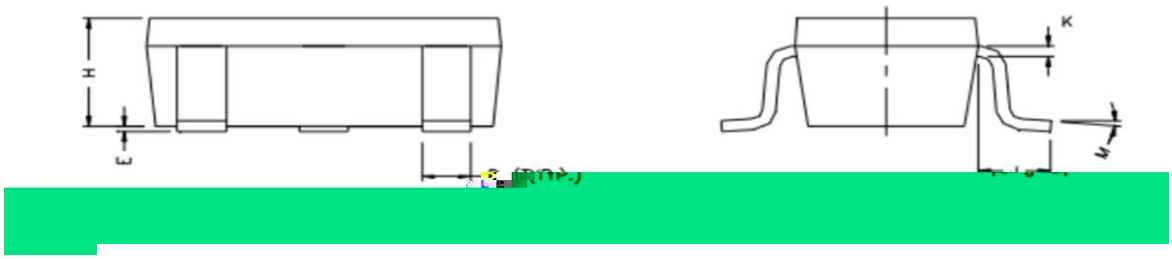


Figure6. Capacitance

Mechanical Data

SOT-23 Package Outline(Unit:mm)





REF.	Millimeter		REF.	Millimete	
	Min.	Max.		Min.	Max.
A	2.80	3.00	G	1.80	2.00
B	2.50	2.50	H	0.80	1.10
C	1.20	1.40	K	0.10	0.20
D	0.30	0.50	J	0.85	0.90
E	0	0.10	L	0.95	0.98
F	0.40	0.55	M	0°	10°

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